HIGH-SPEED 4K x 16 DUAL-PORT STATIC RAM

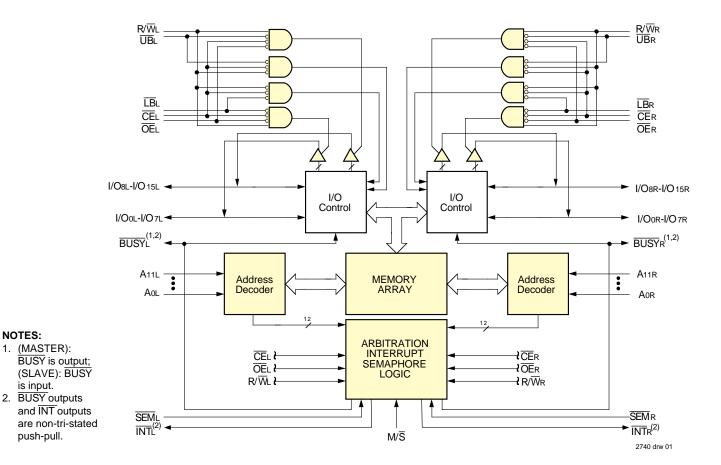
IDT7024S/L

FEATURES:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed access
 - Military: 20/25/35/55/70ns (max.)
 - Commercial: 15/17/20/25/35/55ns (max.)
- Low-power operation
 - IDT7024S
 - Active: 750mW (typ.) Standby: 5mW (typ.)
 - IDT7024L
 - Active: 750mW (typ.) Standby: 1mW (typ.)
- Separate upper-byte and lower-byte control for multiplexed bus compatibility
- IDT7024 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading

- more than one device
- $M/\overline{S} = H$ for \overline{BUSY} output flag on Master $M/\overline{S} = L$ for \overline{BUSY} input on Slave
- · Busy and Interrupt Flags
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Devices are capable of withstanding greater than 2001V electrostatic discharge.
- Fully asynchronous operation from either port
- Battery backup operation—2V data retention
- TTL-compatible, single 5V (±10%) power supply
- Available in 84-pin PGA, 84-pin quad flatpack, 84-pin PLCC, and 100-pin Thin Quad Plastic Flatpack
- Industrial temperature range (-40°C to +85°C) is available, tested to military electrical specifications

FUNCTIONAL BLOCK DIAGRAM



The IDT logo is a registered trademark of Integrated Device Technology, Inc.

OCTOBER 1996

NOTES:

(MASTER):

is input.

push-pull.

DESCRIPTION:

The IDT7024 is a high-speed 4K x 16 Dual-Port Static 64K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit or more word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, errorfree operation without the need for additional discrete logic.

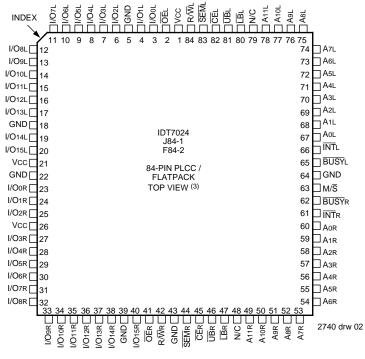
This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by chip enable (\overline{CE}) permits the on-chip circuitry of each port to enter

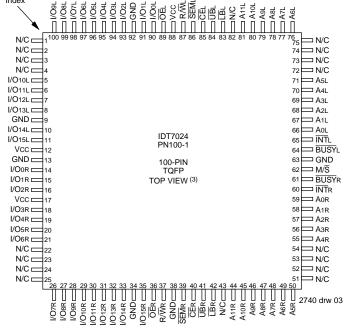
a very low standby power mode.

Fabricated using IDT's CMOS high-performance technol RAM. The IDT7024 is designed to be used as a stand-alone ogy, these devices typically operate on only 750mW of power. Low-power (L) versions offer battery backup data retention capability with typical power consumption of 500µW from a 2V

> The IDT7024 is packaged in a ceramic 84-pin PGA, an 84pin quad flatpack, an 84-pin PLCC, and a 100-pin TQFP. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

PIN CONFIGURATIONS (1,2)





NOTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. This text does not indicate orientation of the actual part-marking.

6.15

2

PIN CONFIGURATIONS (CONT'D) (1,2)

	63	61	60	58	55	54	51	48	46	45	42
11	I/O7L	I/O ₅ L	I/O4L	I/O ₂ L	I/O ₀ L	ŌĒL	SEML	ŪB∟	A11L	A10L	A7L
	66	64	62	59	56	49	50	47	44	43	40
10	I/O10L	I/O8L	I/O6L	I/O3L	I/O1L	ŪBL	CEL	N/C	A9L	A8L	A5L
	67	65			57	53	52			41	39
09	I/O11L	I/O9L			GND		A6L	A4I			
	69	68	-				38	37			
80	I/O13L	I/O12L								АзL	A2I
	72	71	73			35	34				
07	I/O15L	I/O14L	Vcc			BUSYL	AoL	ĪNT			
	75	70	74		IDT7024 G84-3 32						36
06	I/O ₀ R	GND	GND		8 T	GND	M/S	A11			
	76	77	78						28	29	30
05	I/O1R	I/O ₂ R	Vcc						A ₀ R	ĪNTR	BUS
	79	80								26	27
04	I/O3R	I/O4R								A2R	A1F
	81	83	-		7	11	12	1		23	25
03	I/O ₅ R	I/O7R			GND	GND	SEMR			A ₅ R	Азғ
	82	1	2	5	8	10	14	17	20	22	24
02	I/O6R	I/O9R	I/O10R	I/O13R	I/O15R	R/WR	UB R	A11R	A8R	A6R	A4F
	84	3	4	6	9	15	13	16	18	19	21
01	I/O8R	I/O11R	I/O12R	I/O14R	ŌĒR	LBR	CER	N/C	A10R	A9R	A7F
1	A	В	С	D	E	F	G	Н	J	K	L
/ ex											

NOTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. This text does not indicate orientation of the actual part-marking.

PIN NAMES

Left Port	Right Port	Names
CEL	CER	Chip Enable
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
A0L – A11L	A0R – A11R	Address
I/O0L — I/O15L	I/O0R - I/O15R	Data Input/Output
SEML	<u>SEM</u> R	Semaphore Enable
ŪBL	UB r	Upper Byte Select
LBL	LB r	Lower Byte Select
ĪNTL	ĪNTr	Interrupt Flag
BUSYL	BUSYR	Busy Flag
M	I/S	Master or Slave Select
V	CC	Power
GI	ND	Ground

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Ambient Temperature	GND	Vcc
Military	−55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

2740 drw 04

2740 tbl 02

2740 tbl 1

TRUTH TABLE I - NON-CONTENTION READ/WRITE CONTROL

		Inpu	ıts ⁽¹⁾			Out	outs	
CE	R/W	ŌĒ	ŪB	ĪΒ	SEM	I/O8-15	I/O ₀₋₇	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Н	DATAout	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High-Z	DATAout	Read Lower Byte Only
L	Н	L	L	L	Н	DATAout	DATAout	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled
NOTE:	•		•	•	•	•	•	2740 tbl 03

1. AOL — A11L are not equal to AOR — A11R.

TRUTH TABLE II – SEMAPHORE READ/WRITE CONTROL(1)

		Inp	Inputs		Outp	outs		
CE	R/₩	ŌĒ	B	<u>ГВ</u>	SEM	I/O8-15	I/O ₀₋₇	Mode
Н	Н	L	Х	Х	L	DATAout	DATAOUT	Read Semaphore Flag Data Out
Х	Н	L	Н	Н	L	DATAout	DATAOUT	Read Semaphore Flag Data Out
Н	ſ	Х	Х	Х	L	DATAIN	DATAIN	Write I/O ₀ into Semaphore Flag
Х	f	Х	Н	Н	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	Χ	L	_	_	Not Allowed
L	Х	Х	Χ	L	L	_	_	Not Allowed

NOTE:

2740 tbl 04

1. There are eight semaphore flags written to via I/O₀ and read from all of the I/O's (I/O₀ - I/O₁₅). These eight semaphores are addressed by A₀ - A₂.

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	>
ТА	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	ç
Тѕтс	Storage Temperature	-55 to +125	-65 to +150	°C
Іоит	DC Output Current	50	50	mA

NOTES: 2740 tbl 05

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc +0.5V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20ma for the period over VTERM \geq Vcc + 0.5V.

RECOMMENDED DC OPERATING **CONDITIONS**

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
ViH	Input High Voltage	2.2		6.0 ⁽²⁾	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

NOTES:

2740 tbl 06

- 1. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 0.5V.

CAPACITANCE⁽¹⁾

 $(TA = +25^{\circ}C, F = 1.0MHZ) TQFP ONLY$

(-,			
Symbol	Parameter	Condition ⁽²⁾ Max. VIN = 3dV 9		Unit
CIN	Input Capacitance	VIN = 3dV	9	рF
Соит	Output Capacitance	Vout = 3dV	10	рF

NOTES:

- 1. This parameter are determined by device characterization, but is not production tested.
- 2. 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (Vcc = $5.0V \pm 10\%$)

			IDT7	024S	IDT70)24L	
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	_	10	_	5	μΑ
ILO	Output Leakage Current	$\overline{\text{CE}}$ = VIH, VOUT = 0V to VCC	_	10	_	5	μΑ
Vol	Output Low Voltage	IOL = 4mA	_	0.4	-	0.4	V
Vон	Output High Voltage	Iон = -4mA	2.4	_	2.4	_	V

NOTE:

2740 tbl 08

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE⁽¹⁾ (Vcc = $5.0V \pm 10\%$)

		Test			7024 Com'l.	. Only	Com	4X17 'I. Only		4X20	702	4X25	
Symbol	Parameter	Condition	Versi	on	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Typ. ⁽²	⁾ Max.	Тур.	⁽²⁾ Max.	Unit
Icc	Dynamic Operating Current	CE _{"A"=VIL} , Outputs Open SEM = VIH	MIL	S L	_ _		_		160 160	370 320	155 155	340 280	mA
	(Both Ports Active)	$f = fMAX^{(3)}$	COM	S L	170 170	310 260	170 170	310 260	160 160	290 240	155 155	265 220	
ISB1	Standby Current (Both Ports — TTL	$\overline{CER} = \overline{CEL} = VIH$ $\overline{SEMR} = \overline{SEML} = VIH$	MIL	S L					20 20	90 70	16 16	80 65	mA
	Level Inputs)	$f = fMAX^{(3)}$	СОМ	S L	20 20	60 50	20 20	60 50	20 20	60 50	16 16	60 50	
ISB2	Standby Current	CE"A"=VIL and CE"B"=VIL ⁽⁵⁾	MIL	S	_	_	_	_	95	240	90	215	mA
	(One Port — TTL	Active Port Outputs Open		L	_		_		95	210	90	180	
	Level Inputs)	$f = fMAX^{(3)}$	СОМ	S	105	190	105	190	95	180	90	170	
		$\overline{\text{SEM}}$ R = $\overline{\text{SEM}}$ L = VIH		L	105	160	105	160	95	150	90	140	
ISB3	Full Standby Current (Both Ports — All	Both Ports CEL and CER ≥Vcc - 0.2V	MIL	S L				1 1	1.0 0.2	30 10	1.0 0.2	30 10	mA
	CMOS Level Inputs)	$ \begin{array}{l} \text{Vin} \geq \text{Vcc} - 0.2 \text{V or} \\ \text{Vin} \leq 0.2 \text{V, f} = 0^{(4)} \\ \hline \text{SEMR} = \overline{\text{SEML}} \geq \text{Vcc} - 0.2 \text{V} \\ \end{array} $	СОМ	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	
ISB4	Full Standby Current (One Port — All CMOS Level Inputs)	CE"A" ≤ 0.2 and CE"B" ≥ VCC - 0.2V (5) SEMR = SEML≥ VCC - 0.2V	MIL	S L	_	_	_	_	90 90	225 200	85 85	200 170	mA
	Civico Level iriputs)	VIN \geq VCC - 0.2V or VIN \leq 0.2V, Active Port Outputs Open, $f = f_{MAX}^{(3)}$	СОМ	S L	100 100	170 140	100 100	170 140	90 90	155 130	85 85	145 120	

NOTES:

2740 tbl 09

- 1. "X" in part numbers indicates power rating (S or L).
- 2. Vcc = 5V, TA = +25°C, and are not production tested. Icc pc = 120mA (typ.)
- 3. At f = fMAX, address and I/O's are cycling at the maximum frequency read cycle of 1/ tRC, and using "AC Test Conditions" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change.
- 5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6.15 5

^{1.} At Vcc ≤ 2.0V input leakages are undefined.

DC ELECTRICAL CHARACTERISTICS OVER THE **OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE**(1)(Cont.) (Vcc = $5.0V \pm 10\%$)

		Test			7024	4X35	7024	1X55	7024 Mil. (
Symbol	Parameter	Condition	Versio	n	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
Icc	Dynamic Operating Current	CE = VIL, Outputs Open SEM = VIH	MIL.	S L	150 150	300 250	150 150	300 250	140 140	300 250	mA
	(Both Ports Active)	$f = fMAX^{(3)}$	COM'L.	S L	150 150	250 210	150 150	250 210	_	_	
ISB1	Standby Current (Both Ports — TTL	CEL = CER = VIH SEMR = SEML = VIH	MIL.	S L	13 13	80 65	13 13	80 65	10 10	80 65	mA
	Level Inputs)	$f = fMAX^{(3)}$	COM'L.	S L	13 13	60 50	13 13	60 50	_	_	
ISB2	Standby Current	\overline{CE} "A"=VIL and \overline{CE} "B"=VIH $^{(5)}$	MIL.	S	85	190	85	190	80	190	mΑ
	(One Port — TTL	Active Port Outputs Open		L	85	160	85	160	80	160	
	Level Inputs)	$f = fMAX^{(3)}$	COM'L.	S	85	155	85	155	_	_	
		$\overline{\text{SEM}}R = \overline{\text{SEM}}L = VIH$		L	85	130	85	130	_	_	
ISB3	Full Standby Current (Both Ports — All	Both Ports CEL and CER ≥ Vcc - 0.2V	MIL.	S L	1.0 0.2	30 10	1.0 0.2	30 10	1.0 0.2	30 10	mA
	CMOS Level Inputs)		COM'L.	S L	1.0 0.2	15 5	1.0 0.2	15 5	_	_ _	
ISB4	Full Standby Current (One Port — All	<u>CE</u> "A" ≤ 0.2 and <u>CE</u> "B" ≥ VCC - 0.2V ⁽⁵⁾	MIL.	S L	80 80	175 150	80 80	175 150	75 75	175 150	mA
	CMOS Level Inputs)	SEMR = SEML ≥ VCC - 0.2V									
		VIN ≥ VCC - 0.2V or	COM'L.	S	80	135	80	135	_	_	
		$\begin{aligned} &\text{VIN} \leq 0.2V, \\ &\text{Active Port Outputs Open,} \\ &f = f_{\text{MAX}}(^{3)} \end{aligned}$		L	80	110	80	110		_	

NOTES:

2740 tbl 10

- "X" in part numbers indicates power rating (S or L). Vcc=5V, $Ta=+25^{\circ}C$, and are not production tested. Iccdc=120mA (typ.)
- At f = fMAX, address and I/O's are cycling at the maximum frequency read cycleof 1/tRC, and using "AC Test Conditions" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change.
- 5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES (L Version Only) $(VLC = 0.2V, VHC = VCC - 0.2V)^{(4)}$

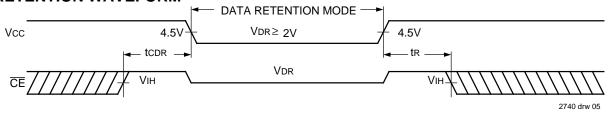
Symbol	Parameter	Test Condi	Min.	Typ. ⁽¹⁾	Max.	Unit	
VDR	Vcc for Data Retention	Vcc = 2V		2.0	_	_	V
ICCDR	Data Retention Current	CE ≥ VHC	MIL.	_	100	4000	μΑ
		$VIN \ge VHC \text{ or } \le VLC$	COM'L.		100	1500	
tcdr ⁽³⁾	Chip Deselect to Data Retention Time	SEM ≥ VHC		0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			tRC ⁽²⁾		_	ns

NOTES:

2740 tbl 11

- $TA = +25^{\circ}C$, VCC = 2V, and are by characterization but are not production tested.
- 2. tRC = Read Cycle Time
- 3. This parameter is guaranteed by device characterization but are not production tested.
- 4. At Vcc ≤ 2.0V, input leakages are not defined.

DATA RETENTION WAVEFORM



AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2
,	2740 tbl 12

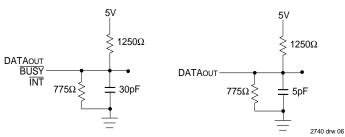


Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLZ, tHZ, tWZ, tOW) Including scope and Jig

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE⁽⁴⁾

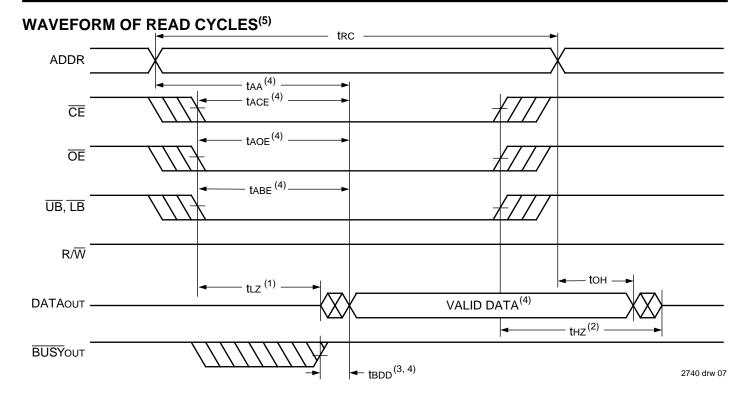
		IDT7024X15 Com'l. Only			24X17 I. Only	IDT70	24X20	IDT70	24X25	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE										
trc	Read Cycle Time	15		17	_	20	_	25	_	ns
t AA	Address Access Time	_	15	_	17	_	20	_	25	ns
tACE	Chip Enable Access Time ⁽³⁾	_	15	_	17	_	20	_	25	ns
tabe	Byte Enable Access Time ⁽³⁾	_	15		17	_	20	_	25	ns
taoe	Output Enable Access Time	_	10	_	10	_	12	_	13	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	3	_	ns
tLZ	Output Low-Z Time ^(1, 2)	3	_	3	_	3	_	3	_	ns
tHZ	Output High-Z Time ^(1, 2)	_	10	_	10	_	12	_	15	ns
tpu	Chip Enable to Power Up Time ^(1,2)	0	_	0	_	0	_	0	_	ns
tPD	Chip Disable to Power Down Time ^(1,2)	_	15	_	17	_	20	_	25	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10	_	10	_	10	<u> </u>	10	_	ns
tsaa	Semaphore Address Access ⁽³⁾	_	15	_	17	_	20	_	25	ns

		IDT70	24X35	IDT70	24X55	1	24X70 Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CY	CLE							
trc	Read Cycle Time	35	_	55	_	70	_	ns
tAA	Address Access Time	_	35	_	55	_	70	ns
tace	Chip Enable Access Time ⁽³⁾	_	35	_	55	_	70	ns
tabe	Byte Enable Access Time ⁽³⁾	T -	35	_	55	_	70	ns
taoe	Output Enable Access Time	T —	20	_	30	_	35	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	ns
tLZ	Output Low-Z Time ^(1, 2)	3	_	3	_	3	_	ns
tHZ	Output High-Z Time ^(1, 2)	_	15	_	25	_	30	ns
tpu	Chip Enable to Power Up Time ^(1,2)	0	_	0	_	0	_	ns
tPD	Chip Disable to Power Down Time ^(1,2)	_	35	_	50	_	50	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	15	_	15	_	15	_	ns
tsaa	Semaphore Address Access ⁽³⁾		35		55	_	70	ns

NOTES:

2740 tbl 13

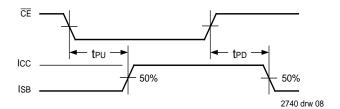
- 1. Transition is measured ±500mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access RAM, $\overrightarrow{CE} = VIL$, \overrightarrow{UB} or $\overrightarrow{LB} = VIL$, and $\overrightarrow{SEM} = VIH$. To access semaphore, $\overrightarrow{CE} = VIH$ or \overrightarrow{UB} & $\overrightarrow{LB} = VIH$, and $\overrightarrow{SEM} = VIH$.
- 4. "X" in part numbers indicates power rating (S or L).



NOTES:

- Timing depends on which signal is asserted last, \(\overline{CE}\), \(\overline{OE}\), \(\overline{LB}\), or \(\overline{UB}\).
 Timing depends on which signal is de-asserted first, \(\overline{CE}\), \(\overline{OE}\), \(\overline{LB}\), or \(\overline{UB}\).
- 3. tbdd delay is required only in cases where opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tabe, tace, tace, tac or tbdd.
- 5. $\overline{SEM} = VIH$.

TIMING OF POWER-UP POWER-DOWN



AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE⁽⁵⁾

		IDT70: Com'l	_	_	24X17 . Only	IDT70	24X20	IDT70	24X25	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE C	YCLE		-							
twc	Write Cycle Time	15	_	17	_	20	_	25	_	ns
tEW	Chip Enable to End-of-Write ⁽³⁾	12	_	12	_	15	_	20	_	ns
taw	Address Valid to End-of-Write	12	_	12	_	15	_	20	_	ns
tas	Address Set-up Time ⁽³⁾	0	_	0	_	0	_	0	_	ns
twp	Write Pulse Width	12	_	12	_	15	_	20	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	10	_	10	_	15	_	15	_	ns
tHZ	Output High-Z Time ^(1, 2)	_	10		10	_	12	_	15	ns
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	0	_	0	_	ns
twz	Write Enable to Output in High-Z ^(1, 2)	_	10	_	10	_	12	_	15	ns
tow	Output Active from End-of-Write ^(1, 2, 4)	0		0	_	0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		5		5		ns
tsps	SEM Flag Contention Window	5	_	5	_	5	_	5	_	ns

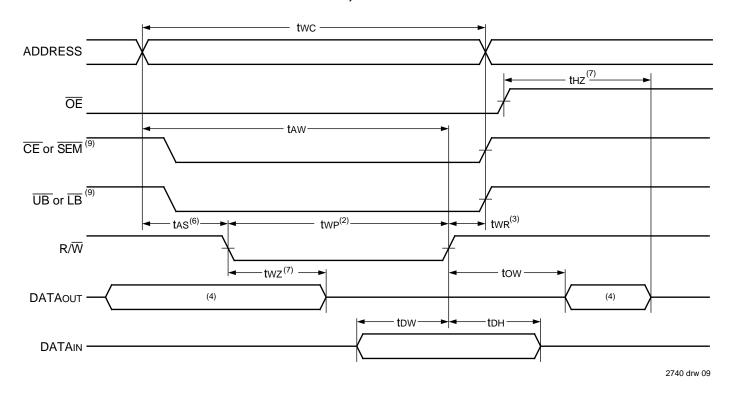
		IDT70	24X35	IDT70	24X55	IDT70: Mil. (_	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE C	YCLE							
twc	Write Cycle Time	35	_	55	_	70		ns
tew	Chip Enable to End-of-Write ⁽³⁾	30	_	45	_	50	_	ns
taw	Address Valid to End-of-Write	30	_	45	_	50	_	ns
tas	Address Set-up Time ⁽³⁾	0	_	0	_	0	_	ns
twp	Write Pulse Width	25	_	40	_	50	_	ns
twr	Write Recovery Time	0	_	0	_	0		ns
tow	Data Valid to End-of-Write	15	_	30	_	40	_	ns
tHZ	Output High-Z Time ^(1, 2)	_	15	_	25	_	30	ns
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	0	_	ns
twz	Write Enable to Output in High-Z ^(1, 2)	_	15	_	25	_	30	ns
tow	Output Active from End-of-Write ^(1, 2, 4)	0	_	0	_	0	_	ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	5	_	ns
tsps	SEM Flag Contention Window	5		5	_	5	_	ns

NOTES

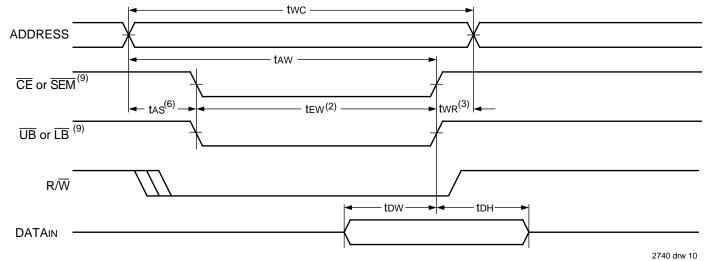
2740 tbl 14

- $1. \quad \text{Transition is measured } \pm 500 \text{mV from Low or High-impedance voltage with the Output Test Load (Figure 2)}.$
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access RAM, $\overline{CE} = VIL$, \overline{UB} or $\overline{LB} = VIL$, $\overline{SEM} = VIH$. To access semaphore, $\overline{CE} = VIH$ or $\overline{UB} \& \overline{LB} = VIH$, and $\overline{SEM} = VIL$. Either condition must be valid for the entire tew time.
- 4. The specification for toh must be met by the device supplying write data to the RAM under all operating conditions. Although toh and tow values will vary over voltage and temperature, the actual toh will always be smaller than the actual tow.
- 5. "X" in part numbers indicates power rating (S or L).

TIMING WAVEFORM OF WRITE CYCLE NO. 1, R/W CONTROLLED TIMING(1,5,8)



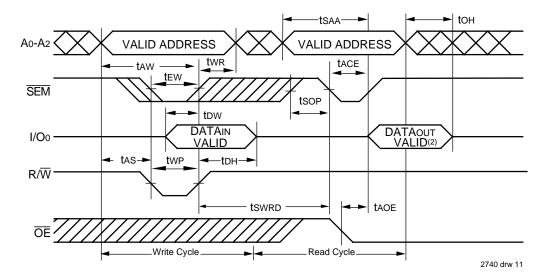
TIMING WAVEFORM OF WRITE CYCLE NO. 2, $\overline{\text{CE}}$, $\overline{\text{UB}}$, $\overline{\text{LB}}$ CONTROLLED TIMING^(1,5)



NOTES:

- 1. R/\overline{W} or \overline{CE} or \overline{UB} & \overline{LB} must be High during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a Low $\overline{\mathsf{UB}}$ or $\overline{\mathsf{LB}}$ and a Low $\overline{\mathsf{CE}}$ and a Low $R\overline{\mathsf{W}}$ for memory array writing cycle.
- 3. twn is measured from the earlier of \overline{CE} or R/\overline{W} (or \overline{SEM} or R/\overline{W}) going High to the end-of-write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM Low transition occurs simultaneously with or after the R/W Low transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, $\overline{\text{CE}}$, $\overline{\text{R/W}}$, $\overline{\text{UB}}$, or $\overline{\text{LB}}$.
- 7. This parameter is guaranted by device characterization, but is not production tested. Transition is measured +/- 500mV steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is Low during R/W controlled write cycle, the write pulse width must be the larger of twp for (twz + tbw) to allow the I/O drivers to turn off and data to be placed on the bus for the required tbw. If \overline{OE} is High during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, $\overline{\text{CE}} = \text{ViL}$, $\overline{\text{UB}}$ or $\overline{\text{LB}} = \text{ViL}$, and $\overline{\text{SEM}} = \text{ViH}$. To access Semaphore, $\overline{\text{CE}} = \text{ViH}$ or $\overline{\text{UB}}$ & $\overline{\text{LB}} = \text{ViH}$, and $\overline{\text{SEM}} = \text{ViL}$. tew must be met for either condition.

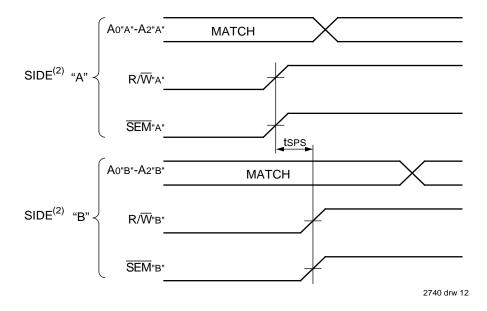
TIMING WAVEFORM OF SEMAPHORE READ AFTER WRITE TIMING, EITHER SIDE(1)



NOTES:

- 1. $\overline{CE} = VIH \text{ or } \overline{UB} \& \overline{LB} = VIH \text{ for the duration of the above timing (both write and read cycle).}$
- 2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

TIMING WAVEFORM OF SEMAPHORE WRITE CONTENTION(1,3,4)



NOTES:

- 1. DOR = DOL = VIL, $\overline{\text{CE}}$ R = $\overline{\text{CE}}$ L = VIH, or both $\overline{\text{UB}}$ & $\overline{\text{LB}}$ = VIH, Semaphore Flag is released from both sides (reads as ones from both sides) at cycle start.
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from R/WA or SEMA going High to R/WB or SEMB going High.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the Semaphore flag.

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (6)

			24X15 I Only		24X17 I Only	IDT70	24X20	IDT7024X25		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIM	ING (M/S = VIH)									
t BAA	BUSY Access Time from Address Match	_	15		17	_	20	_	20	ns
tBDA	BUSY Disable Time from Address Not Matched	_	15		17	_	20	_	20	ns
tBAC	BUSY Access Time from Chip Enable Low	_	15		17		20	_	20	ns
tBDC	BUSY Disable Time from Chip Enable High	_	15	_	17	_	17	_	17	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5	_	5	_	5	_	ns
tBDD	BUSY Disable to Valid Data(3)	_	18	_	18	_	30	_	30	ns
twH	Write Hold After BUSY ⁽⁵⁾	12	_	13	_	15	_	17		ns
BUSY TIM	ING (M/S = VIL)									
twB	BUSY Input to Write ⁽⁴⁾	0	_	0	_	0	_	0	_	ns
twH	Write Hold After BUSY ⁽⁵⁾	12	_	13	_	15	_	17	_	ns
PORT-TO-	PORT DELAY TIMING									
twdd	Write Pulse to Data Delay ⁽¹⁾		30	_	30		45	_	50	ns
tDDD	Write Data Valid to Read Data Delay ⁽¹⁾	_	25	_	25	_	35	_	35	ns

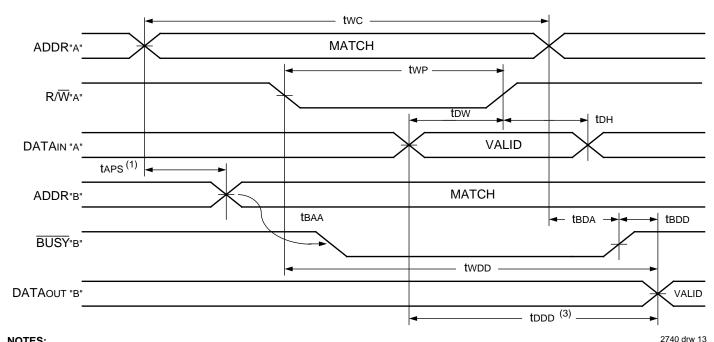
		IDT70	24X35	IDT70	24X55	_	24X70 Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIM	NING (M/S = VIH)							
tbaa	BUSY Access Time from Address Match	_	20	_	45	_	45	ns
tBDA	BUSY Disable Time from Address Not Matched	_	20	_	40	_	40	ns
tBAC	BUSY Access Time from Chip Enable Low	_	20	_	40	_	40	ns
tBDC	BUSY Disable Time from Chip Enable High	_	20	_	35	_	35	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5	_	5	_	ns
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	35		40	_	45	ns
twн	Write Hold After BUSY ⁽⁵⁾	25	_	25	_	25	_	ns
BUSY TIN	IING (M/S = VIL)							
twB	BUSY Input to Write ⁽⁴⁾	0	_	0	_	0	_	ns
twH	Write Hold After BUSY ⁽⁵⁾	25	_	25	_	25	_	ns
PORT-TO	-PORT DELAY TIMING							
twdd	Write Pulse to Data Delay ⁽¹⁾	_	60		80		95	ns
tDDD	Write Data Valid to Read Data Delay ⁽¹⁾	_	45	_	65	_	80	ns

NOTES:

2740 tbl 15

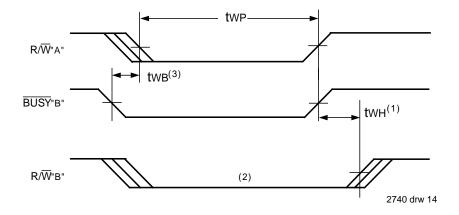
- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Read With BUSY (M/S = VIH)" or "Timing Waveform of Write With Port-To-Port Delay (M/S = VIL)".
- 2. To ensure that the earlier of the two ports wins.
- 3. tBDD is a calculated parameter and is the greater of 0ns, twpd twp (actual), or tpdp tpw (actual).
- 4. To ensure that the write cycle is inhibited on port "B" during contention with port "A".
 5. To ensure that a write cycle is completed on port "B" after contention with port "A".
- 6. "X" in part numbers indicates power rating (S or L).

TIMING WAVEFORM OF WRITE WITH PORT-TO-PORT READ AND \overline{BUSY} (M/ \overline{S} = V_{II})(2,4,5)



- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = VIL$ (slave).
- 2. $\overline{CE}L = \overline{CE}R = VIL$.
- 3. \overline{OE} = VIL for the reading port.
 4. If M/\overline{S} = VIL (slave), \overline{BUSY}*B" is an input. Then for this example \overline{BUSY}*A" = VIH and \overline{BUSY}*B" input is shown above.
- 5. All timing is the same for both left and right ports. Port "A" may be either the left or right Port. Port "B" is the port opposite from port "A".

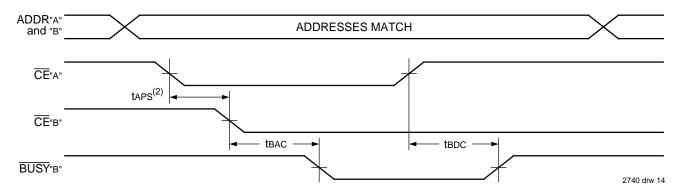
TIMING WAVEFORM OF WRITE WITH BUSY



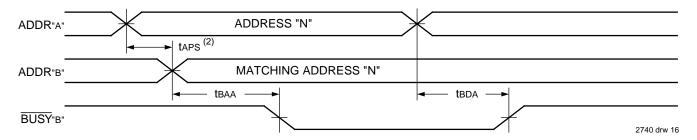
NOTES:

- 1. twn must be met for both BUSY input (slave) and output (master).
- 2. Busy is asserted on port "B" Blocking R/W"B", until BUSY"B" goes High.
- 3. twb is only for the Slave Version.

WAVEFORM OF BUSY ARBITRATION CONTROLLED BY \overline{CE} TIMING (M/ \overline{S} = VIH)(1)



WAVEFORM OF BUSY ARBITRATION CYCLE CONTROLLED BY ADDRESS MATCH TIMING $(M/\overline{S} = Vih)^{(1)}$



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. If tAPS is not satisfied, the busy signal will be asserted on one side or another but there is no guarantee on which side busy will be asserted.

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE⁽¹⁾

		_	IDT7024X15 IDT7024X17 Com'l. Only Com'l. Only		IDT7024X20		IDT7024X25			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRU	PT TIMING									
tas	Address Set-up Time	0	_	0	_	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	0	_	ns
tins	Interrupt Set Time	_	15	_	15	_	20	_	20	ns
tinr	Interrupt Reset Time	_	15	_	15	_	20	_	20	ns

		IDT70	24X35	IDT70	24X55	IDT70 Mil.		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRU	PT TIMING							
tas	Address Set-up Time	0	_	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tins	Interrupt Set Time	_	25	_	40	_	50	ns
tinr	Interrupt Reset Time	_	25		40		50	ns

6.15

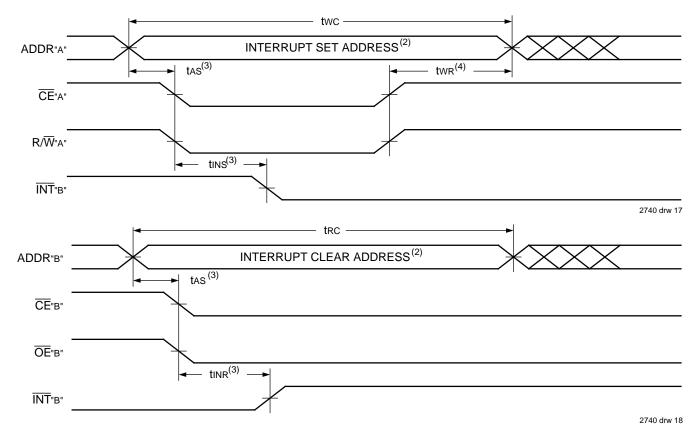
NOTE

1. "X" in part numbers indicates power rating (S or L).

2740 tbl 16

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WAVEFORM OF INTERRUPT TIMING(1)



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. See Interrupt truth table.
- 3. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal (\overline{CE} or R/W) is de-asserted first.

TRUTH TABLES

TRUTH TABLE III — INTERRUPT FLAG(1,4)

	Le	ft Port				R	ight Poi	rt		
R∕WL	CEL	<u>OE</u> ∟	A11L-A0L	ĪNT∟	R/WR	CER	ÖE R	A 11R -A 0R	INT R	Function
L	L	Х	FFF	Χ	Х	Х	Χ	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Χ	Х	Χ	Х	L	L	FFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Χ	Х	L ⁽³⁾	L	L	Х	FFE	Χ	Set Left INTL Flag
Х	L	L	FFE	H ⁽²⁾	Х	Х	Х	Х	Χ	Reset Left INTL Flag

NOTES:

2740 tbl 17

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = VIH$.
- 2. If $\overline{BUSY}L = VIL$, then no change.
- 3. If $\overline{BUSY}R = VIL$, then no change.
- 4. INTR and INTL must be initialized at power-up.

TRUTH TABLE IV — ADDRESS BUSY ARBITRATION

	In	outs	Ou	tputs	
CEL	CER	A0L-A11L A0R-A11R	BUSYL ⁽¹⁾	BUSYR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	Ш	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

2740 tbl 16

- 1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSYx outputs on the IDT7024 are push pull, not open drain outputs. On slaves, the BUSY asserted input internally inhibits write.
- "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable
 after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = Low will result. BUSYL and BUSYR outputs cannot be low
 simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving low regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving low regardless of actual logic level on the pin.

TRUTH TABLE V — EXAMPLE OF SEMAPHORE PROCUREMENT SEQUENCE(1,2)

Functions	Do - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

2740 tbl 19

- 1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7024.
- 2. There are eight semaphore flags written to via I/O0 and read from all the I/O's (I/O0-I/O15). These eight semaphores are addressed by A0 A2.

FUNCTIONAL DESCRIPTION

The IDT7024 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7024 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ High). When a port is enabled, access to the entire memory array is permitted.

INTERRUPTS

If the user chooses to use the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location FFE (HEX), where a write is defined as the $\overline{CE} = R/\overline{W} = V_{IL}$ per the Truth Table. The left port clears the interrupt by access address location FFE access when $\overline{CER} = \overline{OER} = V_{IL}$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to

memory location FFF (HEX) and to clear the interrupt flag (INTR), the right port must access the memory location FFF. The message (16 bits) at FFE or FFF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations FFE and FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table for the interrupt operation.

BUSY LOGIC

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The busy pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of busy logic is not required or desirable for all

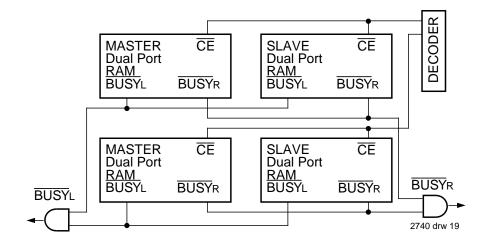


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7024 RAMs.

applications. In some cases it may be useful to logically OR the busy outputs together and use any busy indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of busy logic is not desirable, the busy logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins high. If desired, unintended write operations can be prevented to a port by tying the busy pin for that port low.

The busy outputs on the IDT 7024 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the busy indication for the resulting array requires the use of an external AND gate.

WIDTH EXPANSION WITH BUSY LOGIC MASTER/SLAVE ARRAYS

When expanding an IDT7024 RAM array in width while using busy logic, one master part is used to decide which side of the RAM array will receive a busy indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT7024 RAM the busy pin is an output if the part is used as a master (M/ \overline{S} pin = H), and the busy pin is an input if the part used as a slave (M/ \overline{S} pin = L) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating busy on one side of the array and another master indicating busy on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The busy arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a busy flag to be output from the master before the actual write pulse

can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

SEMAPHORES

The IDT7024 is an extremely fast Dual-Port 4K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table where \overline{CE} and SEM are both high.

Systems which can best use the IDT7024 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7024's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the

maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7024 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

HOW THE SEMAPHORE FLAGS WORK

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active low. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT7024 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the SEM pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, OE, and R/W) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table III). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussing on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side

until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (\overline{SEM}) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (\overline{SEM}) or \overline{OE} to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table III). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag low and the other side high. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay low until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a

resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

USING SEMAPHORES—SOME EXAMPLES

Perhaps the simplest application of semaphores is their application as resource markers for the IDT7024's Dual-Port RAM. Say the 4K x 16 RAM was to be divided into two 2K x 16 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 2K of Dual-Port RAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 2K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 2K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 2K blocks of Dual-Port RAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port RAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

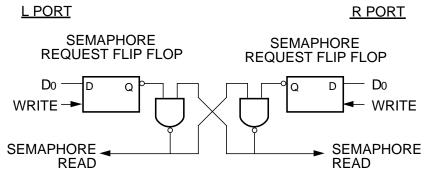
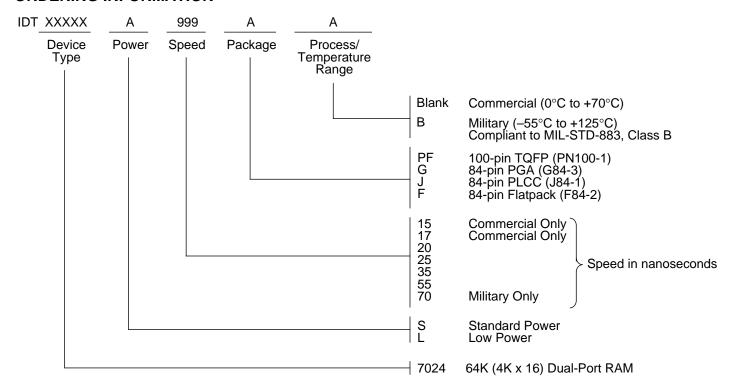


Figure 4. IDT7024 Semaphore Logic

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ORDERING INFORMATION



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